

In The Claims

~~Claim 12 has been amended as follows:~~

12. (Amended) A method for forming aluminum bumps on a semiconductor structure comprising the steps of:

providing a pre-processed semiconductor structure with a plurality of I/O pads on top;

printing a layer of polyimide-containing material having a thickness of at least 5 μm on top of said structure;

forming a plurality of openings on each of said plurality of I/O pads exposed;

filling said plurality of openings with a metal comprising Al;

removing excess metal from areas other than said plurality of openings; and

removing at least partially said layer of polyimide-containing material by a wet etch process.

REMARKS

Thorough examination and careful review of the application by the Examiner is noted and appreciated.